

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously Presented) A semiconductor device comprising:
  - a semiconductor substrate;
  - a first insulating film formed on an upper side of said semiconductor substrate, said first insulating film consisting essentially of ladder-shaped siloxane hydride; and
  - a second insulating film disposed adjacent to said first insulating film, said second insulating film containing oxygen and silicon as constituent elements.
2. (Canceled)
3. (Original) The semiconductor device according to claim 1, wherein said second insulating film comprises a compound selected from the group consisting of SiO<sub>2</sub>, SiOC, SiON and SiOF.
4. (Original) The semiconductor device according to claim 1, further comprising a metal interconnect embedded in a multilayer structure, said multilayer structure comprising said first insulating film and said second insulating film.
5. (Original) The semiconductor device according to claim 1, wherein said semiconductor device is free of a guard ring.
6. (Previously Presented) The semiconductor device according to claim 1, wherein said ladder-shaped siloxane hydride has a dielectric constant of not higher than 2.9.
7. (Original) The semiconductor device according to claim 1, wherein said ladder-shaped siloxane hydride is a film being formed by being baked at a temperature within a range of from 200 degree C to 400 degree C.
8. (Previously Presented) The semiconductor device according to claim 1, wherein said ladder-shaped siloxane hydride has a film density within a range of from 1.50 g/cm<sup>3</sup> to 1.58 g/cm<sup>3</sup>.

9. (Previously Presented) The semiconductor device according to claim 1, wherein said ladder-shaped siloxane hydride has a refraction index at a wavelength of 633 nm within a range of from 1.38 to 1.40.

Claims 10-16. (Cancelled).